

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
20V	0.6Ω @ V _{GS} = 4.5V	0.9A
	0.8Ω @ V _{GS} = 2.5V	0.7A
	1.0Ω @ V _{GS} = 1.8V	0.5A
	1.6Ω @ V _{GS} = 1.5V	0.3A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

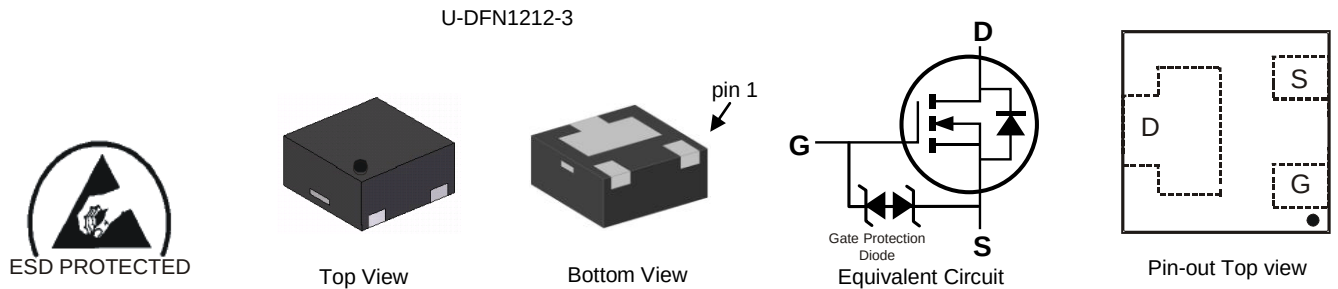
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Load Switch

Features and Benefits

- Low On-Resistance
- Very low Gate Threshold Voltage, 1.0V Max.
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: U-DFN1212-3
- Case Material: Molded Plastic;
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe;
Solderable per MIL-STD-202, Method 208 (e4)
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)



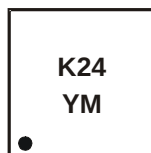
Ordering Information (Note 5)

Part Number	Case	Packaging
DMN2400UFDQ-7	U-DFN1212-3	3,000/Tape & Reel
DMN2400UFDQ-13	U-DFN1212-3	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

U-DFN1212-3



K24 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: C = 2015)
 M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	C	D	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 7) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	0.9	A
		T _A = +70°C		0.7	
Continuous Drain Current (Note 7) V _{GS} = 2.5V	Steady State	T _A = +25°C	I _D	0.7	A
		T _A = +70°C		0.5	
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	3.0	A
Maximum Body Diode Forward Current (Note 7)			I _S	0.8	A

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		P _D	0.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	283	°C/W
Total Power Dissipation (Note 7)		P _D	0.8	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R _{θJA}	147	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	112	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	80 100	nA	V _{DS} = 4.5V, V _{GS} = 0V V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±1.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	0.45	-	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	0.35	0.6	Ω	V _{GS} = 4.5V, I _D = 200mA
		-	0.45	0.8		V _{GS} = 2.5V, I _D = 200mA
		-	0.6	1.0		V _{GS} = 1.8V, I _D = 100mA
		-	0.7	1.6		V _{GS} = 1.5V, I _D = 50mA
		-	0.7	1.6		V _{GS} = 1.5V, I _D = 50mA
Forward Transfer Admittance	Y _{fs}	-	1.4	-	S	V _{DS} = 3V, I _D = 200mA
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	V _{GS} = 0V, I _S = 500mA,
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	-	37.0	-	pF	V _{DS} = 16V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	5.7	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	4.2	-	pF	
Gate Resistance	R _g	-	68	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	-	0.5	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	-	0.07	-	nC	
Gate-Drain Charge	Q _{gd}	-	0.1	-	nC	
Turn-On Delay Time	t _{D(on)}	-	4.06	-	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 47Ω, R _G = 10Ω, I _D = 200mA
Turn-On Rise Time	t _r	-	7.28	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	13.74	-	ns	
Turn-Off Fall Time	t _f	-	10.54	-	ns	

- Notes:
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.

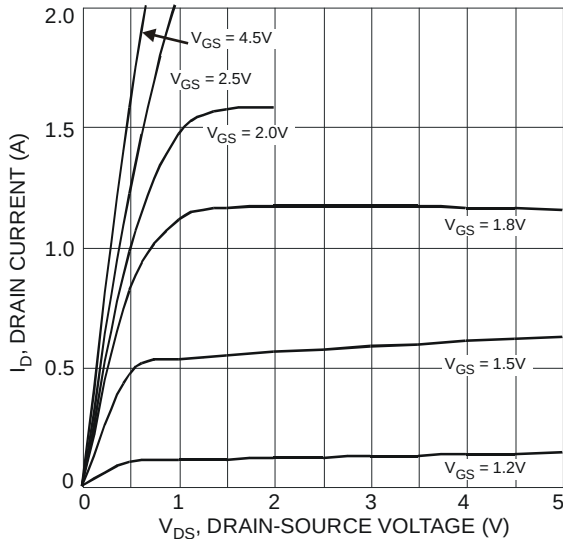


Fig. 1 Typical Output Characteristics

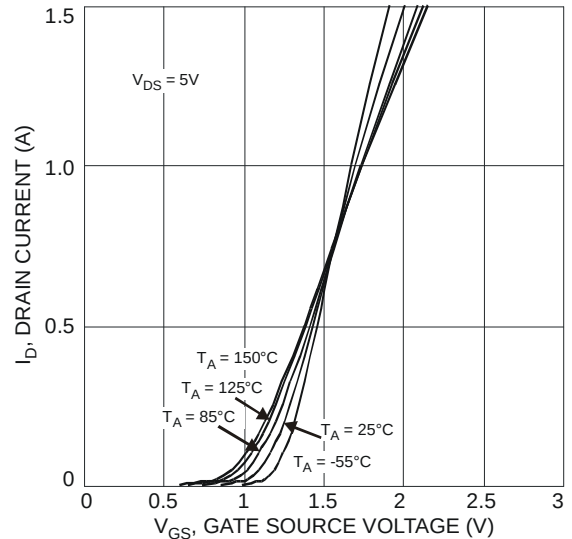


Fig. 2 Typical Transfer Characteristics

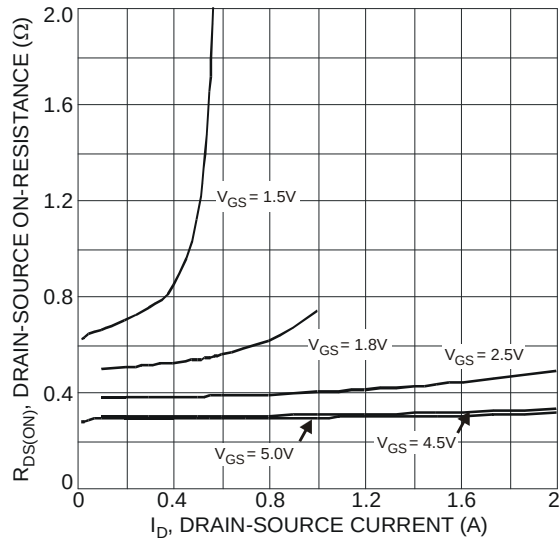


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

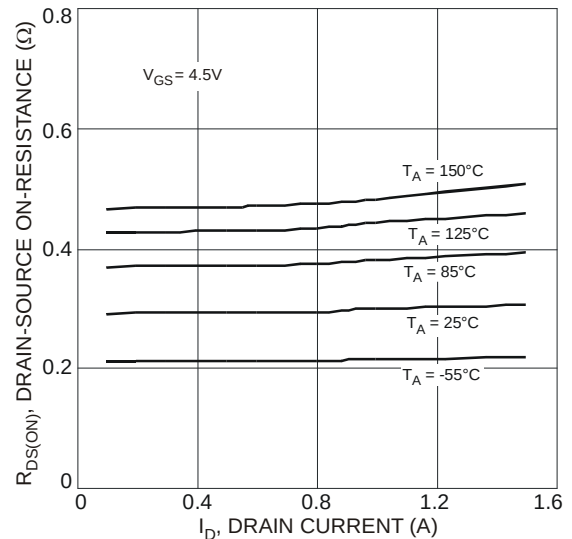


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

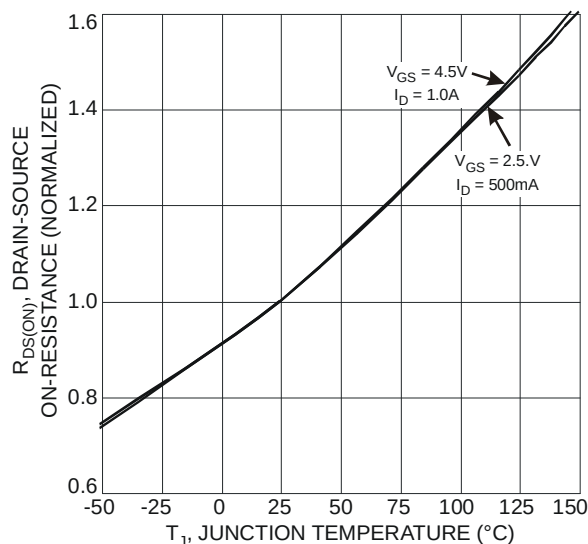


Fig. 5 On-Resistance Variation with Temperature

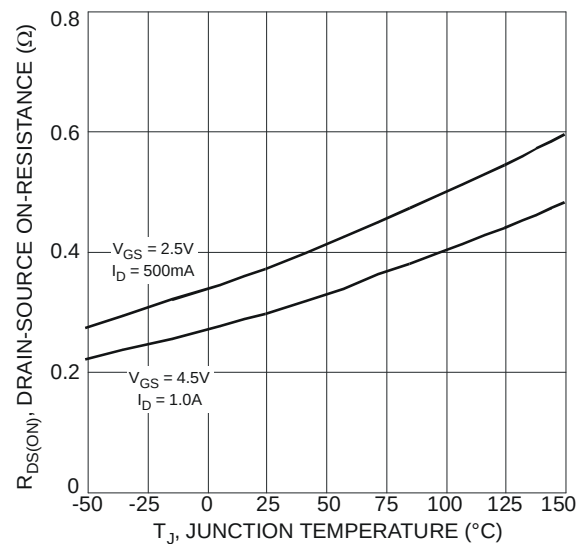


Fig. 6 On-Resistance Variation with Temperature

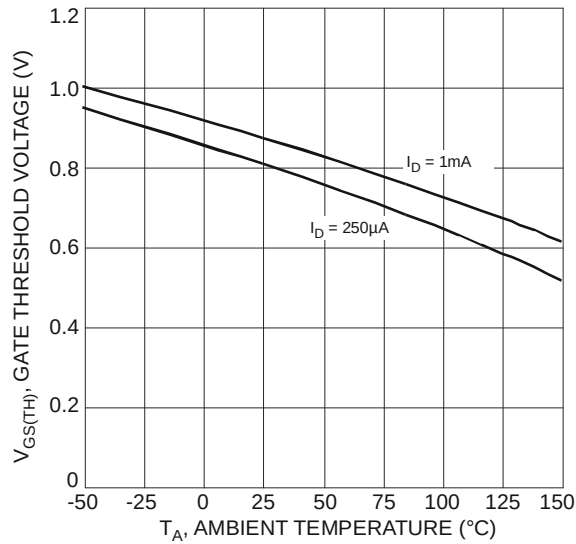


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

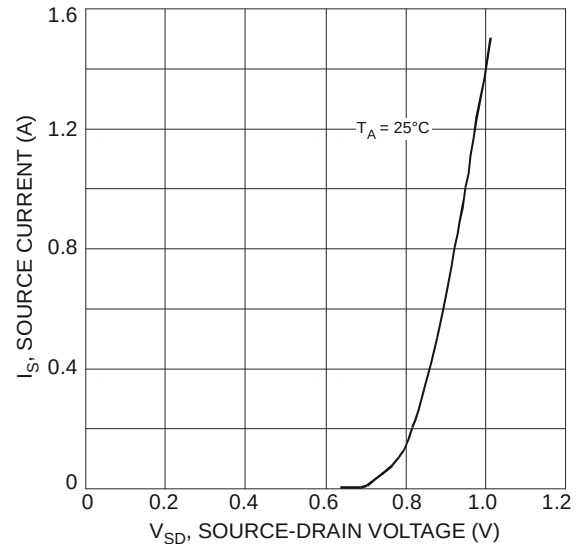


Fig. 8 Diode Forward Voltage vs. Current

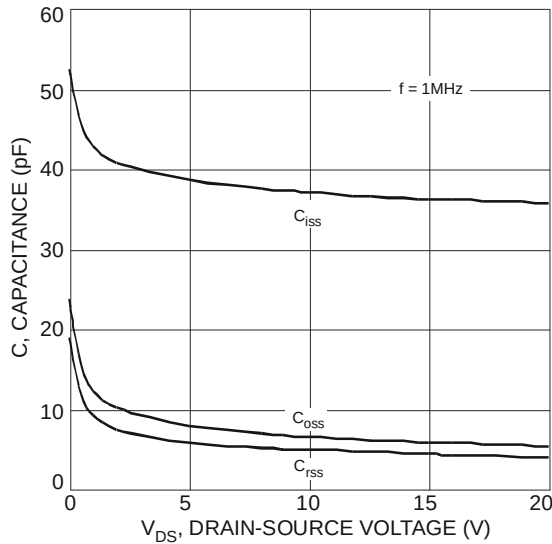


Fig. 9 Typical Capacitance

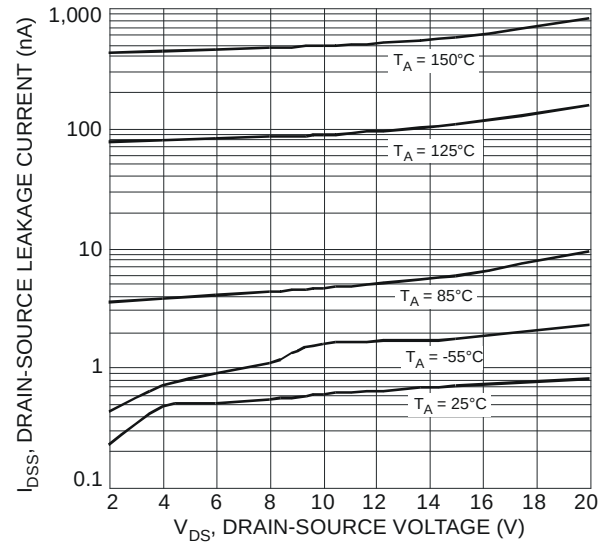


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

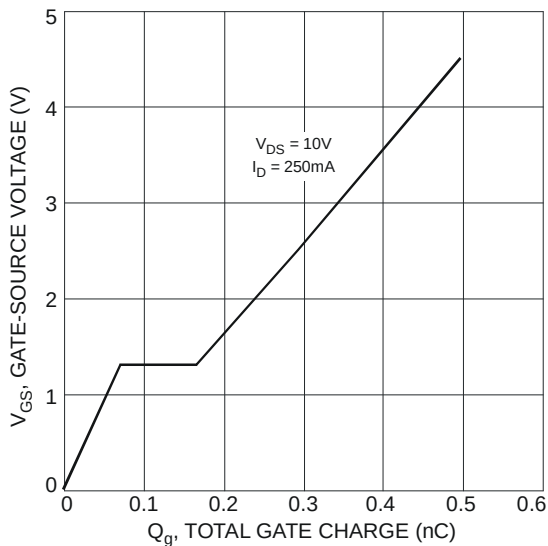


Fig. 11 Gate-Charge Characteristics

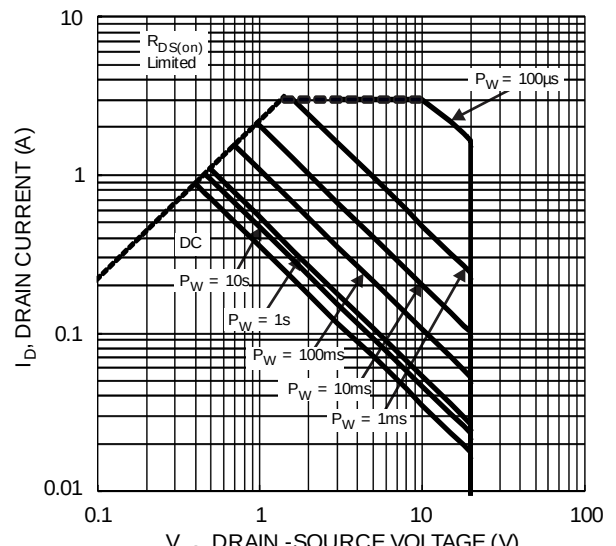
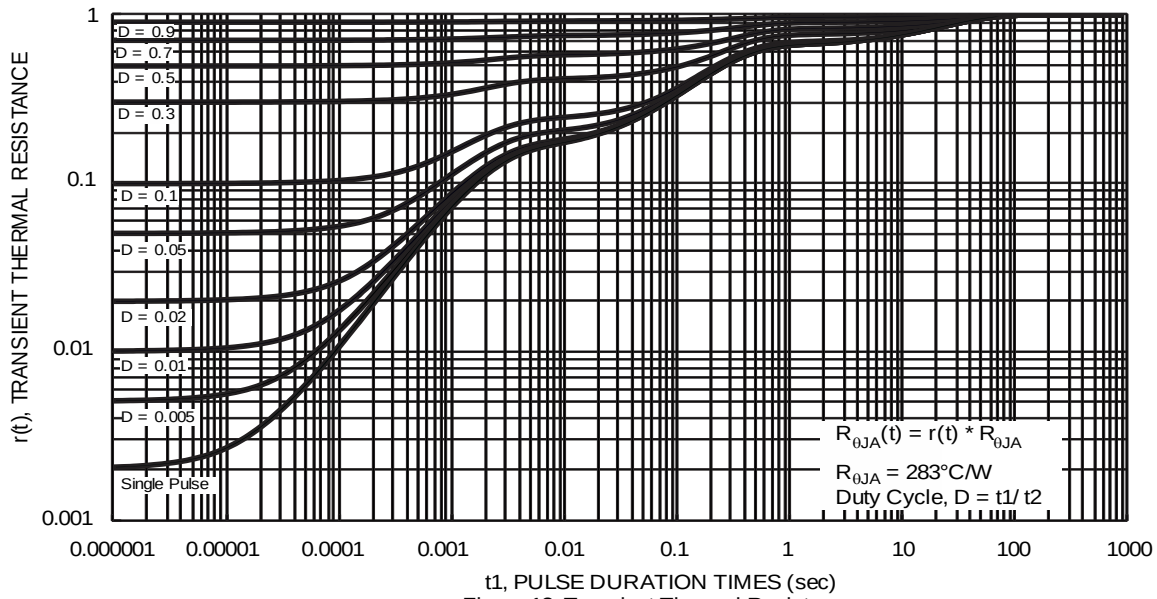
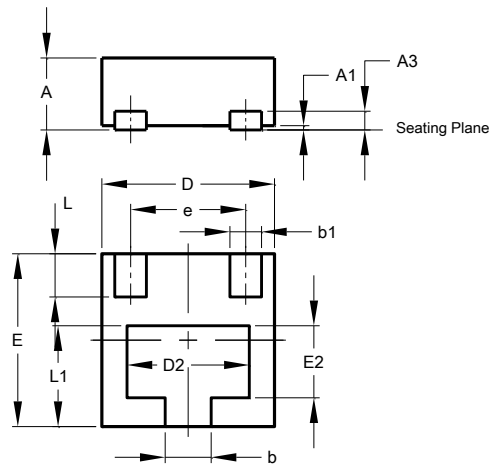


Figure 12 Typical Output Characteristics



Package Outline Dimensions

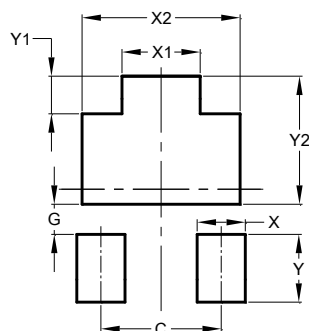
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-DFN1212-3 (Type C)			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	-	-	0.13
b	0.27	0.37	0.32
b1	0.17	0.27	0.22
D	1.15	1.25	1.20
D2	0.75	0.95	0.85
e	-	-	0.80
E	1.15	1.25	1.20
E2	0.40	0.60	0.50
L	0.25	0.35	0.30
L1	0.65	0.75	0.70
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



U-DFN1212-3 (Type C)	
Dimensions	Value
C	0.800
G	0.200
X	0.320
X1	0.520
X2	1.050
Y	0.450
Y1	0.250
Y2	0.850
All Dimensions in mm	

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